

TIOS101, TIOS101x Digital Sensor Output Drivers with Integrated Surge Protection

1 Features

- **Functional Safety-Capable**
 - Documentation available to aid functional safety system design: TIOS101,TIOS1013, TIOS1015
- 7-V to 36-V Supply Voltage
- PNP, NPN or Push-Pull Configurable Output
- Low Residual Voltage of 1.75 V at 250 mA
- 50-mA to 350-mA Configurable Current Limit
- Tolerant to ±65-V Transients < 100 μs
- Reverse Polarity Protection of up to 60 V on VCC, **OUT and GND**
- Integrated EMC Protection on VCC and OUT
 - ±16 kV IEC 61000-4-2 ESD Contact Discharge
 - ±4 kV IEC 61000-4-4 Electrical Fast Transient
 - ±1.2 kV/500 Ω IEC 61000-4-5 Surge
- Fast Demagnetization of Inductive Loads up to 1.5 H
- Large Capacitive Load Driving Capability
- < 2.2-mA Quiescent Supply Current
- Integrated LDO Options for up to 20 mA Current
 - TIOS101: No LDO
 - TIOS1013: 3.3-V LDO
 - TIOS1015: 5-V LDO
- Overtemperature Warning and Thermal Protection
- Fault Indicator
- Extended Ambient Temperature: -40°C to 125°C
- 2.5 mm x 3 mm 10-pin VSON Package

2 Applications

- **Proximity Switches**
- Capacitive and Inductive Sensors
- **Digital Outputs**

3 Description

The TIOS101(x) devices are configurable as highside, low-side or push-pull drivers. These devices are capable of withstanding up to 1.2 kV (500 Ω) of IEC 61000-4-5 surge and feature integrated reverse polarity protection.

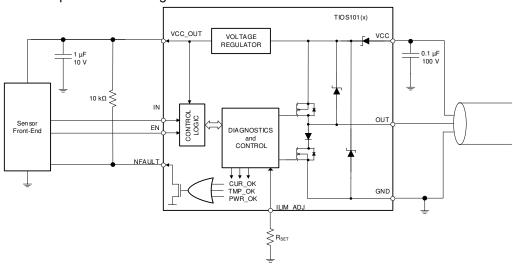
A simple pin-programmable interface allows easy interfacing to the controller circuits. The output current limit can be configured using an external resistor.

Fault reporting and internal protection functions are provided for under voltage, over circuit current and over temperature.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)
TIOS101		
TIOS1013	VSON (10)	2.50 mm x 3.00 mm
TIOS1015		

For all available devices, see the orderable addendum at the end of the data sheet.



Typical Application Diagram



Table of Contents

1 Features	1	8.2 Functional Block Diagrams	9
2 Applications	1	8.3 Feature Description	10
3 Description		8.4 Device Functional Modes	
4 Revision History		9 Application Information Disclaimer	17
5 Pin Configuration and Functions	3	9.1 Application Information	
6 Specifications	4	9.2 Typical Application	
6.1 Absolute Maximum Ratings	4	10 Power Supply Recommendations	
6.2 ESD Ratings		11 Layout	
6.3 Recommended Operating Conditions		11.1 Layout Guidelines	
6.4 Thermal Information		11.2 Layout Example	
6.5 Electrical Characteristics		12 Device and Documentation Support	
6.6 Switching Characteristics		12.1 Receiving Notification of Documentation Update	
6.7 Typical Characteristics		12.2 Support Resources	
7 Parameter Measurement Information		12.3 Trademarks	
8 Detailed Description		12.4 Electrostatic Discharge Caution	
8.1 Overview	9	12.5 Glossary	23
Changes from Revision A (August 2018) to Re	visio		Page
 Added device numbers TIOS1013 and TIOS10 	015 to	the data sheet	1
 Changed all TIOS101-3 To: TIOS1013 and TIC 	DS10 ²	1-5 To: TIOS1015	
Changed Feature From: Reverse Polarity Protein	ection	of up to 55 V on VCC To: Reverse Polarity Protection	
up to 60 V on VCC			1 n of
Changed the Supply voltage values From: MIN	 N = -5		1 n of 1
Changed the Supply voltage values From: MIN Absolute Maximum Ratings	N = -5	55 V, MAX = 50 V To: MIN = -60 V, MAX = 60 V in the	1 n of 1
 Changed the Supply voltage values From: MIN Absolute Maximum Ratings Changed the Voltage difference Max value From the V	N = -5 om: 55	55 V, MAX = 50 V To: MIN = -60 V, MAX = 60 V in the	1 n of 1 ; 4 4
 Changed the Supply voltage values From: MIN Absolute Maximum Ratings Changed the Voltage difference Max value From Changed 55 V To: 60 V in the Leakage current 	N = -5 om: 55 ent Te	55 V, MAX = 50 V To: MIN = -60 V, MAX = 60 V in the 5 V To: 60 V in the <i>Absolute Maximum Ratings</i>	1 on of 1 e 4 4
 Changed the Supply voltage values From: MIN Absolute Maximum Ratings Changed the Voltage difference Max value From: Changed 55 V To: 60 V in the Leakage currer Changed text From: "not exceed 55 V DC at all the control of the contr	N = -5 om: 55 ent Te ny tim	55 V, MAX = 50 V To: MIN = -60 V, MAX = 60 V in the	1 n of1 e445 erse
 Changed the Supply voltage values From: MIN Absolute Maximum Ratings Changed the Voltage difference Max value From: Changed 55 V To: 60 V in the Leakage currer Changed text From: "not exceed 55 V DC at all the control of the contr	om: 55 ent Te ny tim	55 V, MAX = 50 V To: MIN = -60 V, MAX = 60 V in the 5 V To: 60 V in the Absolute Maximum Ratings	1 n of1 e445 erse



5 Pin Configuration and Functions

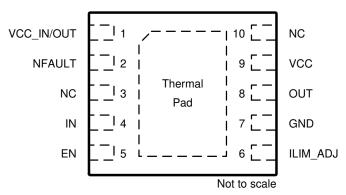


Figure 5-1. DMW Package, 10-Pin (VSON), Top View

Table 5-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.	1 1/0	DESCRIPTION
OUT	8	0	Switch output
VCC	9	POWER	Supply voltage (24 V nominal)
GND	7	POWER	Device ground
EN	5	I	Driver enable input signal from the local controller. Logic low sets the OUT output at Hi-Z. Weak internal pulldown.
IN	4	I	Transmit data input from the local controller. No effect if EN is low. Logic high sets low-side switch. Logic low sets high-side switch. Weak internal pull-up.
VCC_IN/OUT	1	POWER	3.3-V or 5-V linear regulator output; external 3.3-V or 5-V logic supply input for option without LDO.
ILIM_ADJ	6	I	Input for current limit adjustment. Connect resistor R _{SET} between ILIM_ADJ and GND.
NFAULT	2	OPEN-DRAIN	Fault indicator output signal to the microcontroller. A low level indicates either an over- current, an undervoltage in supply or an overtemperature condition. Connect this pin via pull-up resistor to VCC_IN/OUT.
NC	3, 10	_	No internal connection.
Thermal Pad	_	_	Connect to GND plane for optimal thermal and electrical performance



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1) (2)

		MIN	MAX	UNIT
Cumply walks as	Steady state voltage for VCC and OUT	-60	60	V
Supply voltage	Transient pulse width < 100 μs for VCC and OUT	-65	65	V
Voltage difference	V _(VCC) - V _(OUT)		60	V
Logic supply voltage (TIOS101)	VCC_IN	-0.3	6	V
Input logic voltage	IN, EN, ILIM_ADJ	-0.3	6	V
Output current	NFAULT	-5	5	mA
Storage temperature, T _{stg}		-55	170	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with reference to the GND pin, unless otherwise specified.

6.2 ESD Ratings

				VALUE	UNIT
	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	All pins	±4000		
	V _(ESD) Electrostatic discharge	Contact discharge, per IEC 61000-4-2 ^{(2) (3)}		±16000	
V(ESD)		Electrical fast transient, per IEC 61000-4-4 ⁽²⁾	Pins VCC, OUT	±4000	V
	Surge protection with 500 Ω , per IEC 61000-4-5; 1.2/50 μ s ⁽²⁾	and GND	±1200		

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) Minimum 100-nF capacitor is required between VCC and GND. Minimum 1-µF capacitor is required between VCC_IN/OUT and GND.
- (3) Passing level is ±4500 V if the device is powered and EN=IN=HIGH.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _(VCC)	Supply voltage		7	24	36	V
Logio lovel input veltage /TIOS101 enly)		3.3 V configuration	3	3.3	3.6	V
V _(VCC_IN) Logic level input voltage (TIOS101 only)	5 V configuration	4.5	5	5.5	V	
R _{SET}	External resistor for OUT current limit	0		100	kΩ	
1/t _{BIT}	Signaling rate (push-pull mode)				250	kbps
I _(VCC_OUT)	LDO output current (TIOS1013 and TIOS1015 only)				20	mA
T _A	Operating ambient temperature		-40		125	°C
T _J	Junction temperature				150	°C



6.4 Thermal Information

	THERMAL METRIC ⁽¹⁾	TIOS101(x)	UNIT
	I DERIVAL IVIETRIO	DMW (10 Pins)	ONII
R _{0JA}	Junction-to-ambient thermal resistance	68.1	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	60.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	40.6	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	13.4	°C/W
ΨЈВ	Junction-to-board characterization parameter	40.7	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	25.2	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER S	UPPLIES (VCC)		<u> </u>			
	0	EN = LOW, no load		1.5	2.2	mA
I _(VCC) Quiescent supply current		EN = HIGH, no load		2	2.7	mA
LOGIC-LE	VEL INPUTS (EN, IN)		,		'	
V _{IL}	Input logic low voltage				0.8	V
V _{IH}	Input logic high voltage		2			V
R _{PD}	Pull-down (EN) resistance			100		kΩ
R _{PU}	Pull-up (IN) resistance			200		kΩ
CONTROL	OUTPUT (NFAULT)		<u> </u>			
V _{OL}	Output logic low voltage	I _O = 4 mA			0.5	V
l _{OZ}	Output high impedance leakage	Output in Hi-Z, V _O = 0 V or VCC_IN/OUT	-1		1	μΑ
DRIVER O	UTPUT (OUT)				·	
		I = 250 mA			1.75	V
	High-side driver residual voltage	I = 200 mA			1.5	V
\/		I = 100 mA			1.1	V
V _{DS(ON)}	Low-side driver residual voltage	I = 250 mA			1.75	V
		I = 200 mA			1.5	V
		I = 100 mA			1.1	V
1	OLIT multi un/deum eurrent	EN = LOW, IN = LOW, pull-down current	40	50	80	μΑ
l _P	OUT pull-up/down current	EN = LOW, IN = HIGH, pull-up current	40	50	80	μΑ
		R _{SET} = 100 kΩ	35	50	70	mA
$I_{O(LIM)}$	Driver output current limit	$R_{SET} = 0 k\Omega$	300	350	400	mA
		R _{SET} = OPEN ⁽¹⁾	300	350	400	mA
PROTECT	ION CIRCUITS		<u> </u>			
V	VCC under veltage leekeuit	VCC falling; NFAULT = Hi-Z			6	V
$V_{(UVLO)}$	VCC under voltage lockout	VCC rising; NFAULT = LOW			6.5	V
V _{(UVLO,HYS}	VCC under voltage hysteresis	Rising to falling threshold	100			mV
\/	VCC_IN under voltage lockout (No	VCC_IN falling; NFAULT = Hi-Z		2.4		V
V _(UVLO_IN)	LDO option)	VCC_IN rising; NFAULT = LOW		2.5		V
V _{(UVLO,HYS}	VCC_IN under voltage hysteresis (No LDO option)	Rising to falling threshold		100		mV
T _(WRN)	Thermal warning		125			°C
T _(SDN)	Thermal shutdown	Die temperature T _J	150	160		°C
T _(HYS)	Thermal hysteresis for shutdown			10		°C

6.5 Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CO	TEST CONDITIONS			MAX	UNIT
		$V_{(OUT)} < V_{(VCC)}$ or $V_{(OUT)} > V_{(VCC)}$ up to 36 V				50	μΑ
I _{REV} Leakage current in reverse polarity	$V_{(OUT)} < V_{(OUT)}$ or $V_{(OUT)} > V_{(VCC)}$ up to $ 60 \text{ V} $				80	μΑ	
		EN = HIGH, IN = LOW; V _{(OUT t}	_{o VCC)} = 3 V			550	μA
		EN = HIGH, IN = HIGH; V _(OUT to GND) = -3 V				10	μA
LINEAR R	EGULATOR (LDO)					•	
\/	Valtaga ragulatar autaut	TIOS1015		4.75	5	5.25	V
V(VCC_OUT)	Voltage regulator output	TIOS1013		3.13	3.3	3.46	V
\/	Voltage regulator drop-out voltage	L = 20 mA load aurrent	TIOS1015			1.9	V
$V_{(DROP)}$	$(V_{(VCC)} - V_{(VCC_OUT)})$	I _{CC} = 20 mA load current	TIOS1013			2.3	V
REG	Line regulation $(dV_{(VCC_OUT)}/dV_{(VCC)})$	I _(VCC_OUT) = 1 mA			1.7	mV/V	
L _{REG}	Load regulation (dV _(VCC_OUT) / V _(VCC_OUT))	V _(VCC) = 24 V, I _(VCC_OUT) = 100 μA to 20 mA		1%			
PSSR	Power Supply Rejection Ratio	100 kHz, I _(VCC OUT) = 20 mA	100 kHz, I _(VCC, QUT) = 20 mA		40		dB

⁽¹⁾ Current fault indication will be active. Current fault auto recovery will be de-activated.

6.6 Switching Characteristics

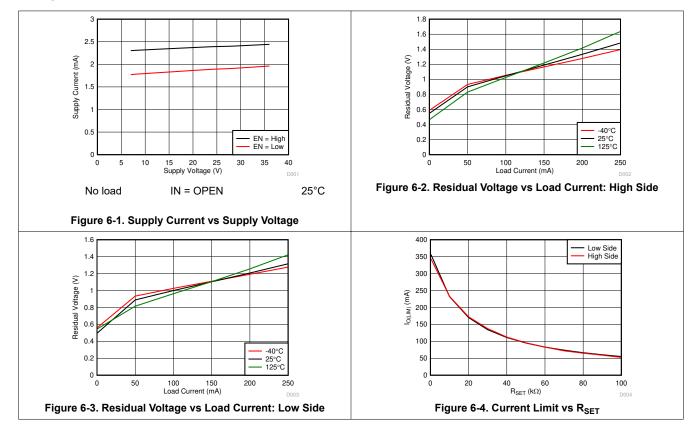
over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Driver propagation delay			600	800	ns
t _{P(skew)}	Driver propagation delay skew. t _{PLH} - t _{PHL}	See Figure 7-1 See Figure 7-2		100		ns
t _{PZH} , t _{PZL}	Driver enable delay	See Figure 7-3 $-R_1 = 2 k\Omega$			4	μs
t _{PHZ} , t _{PLZ}	Driver disable delay	$C_L = 5 \text{ nF}$			4	μs
t _r , t _f	Driver output rise, fall time	$R_{(SET)} = 0 \Omega$			150	ns
$ t_r - t_f $	Difference in rise and fall time	1			50	ns
t _{SC}	Current fault blanking time		175	200		μs
t _{pSC}	Current fault indication delay				260	μs
t _{SCEN}	Current fault driver re-enable wait time			15		ms
t _(UVLO)	OUT re-enable delay after UVLO (1)	V _(UVLO) rising threshold crossing time to OUT enable time	10	30	50	ms

(1) OUT output remains Hi-Z for this time



6.7 Typical Characteristics





7 Parameter Measurement Information

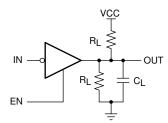


Figure 7-1. Test Circuit for Driver Switching

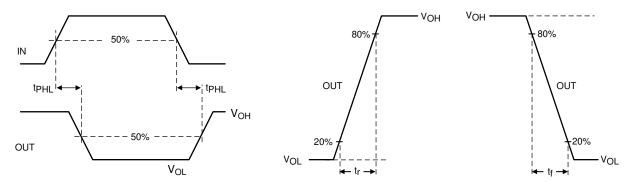


Figure 7-2. Waveforms for Driver Output Switching Measurements

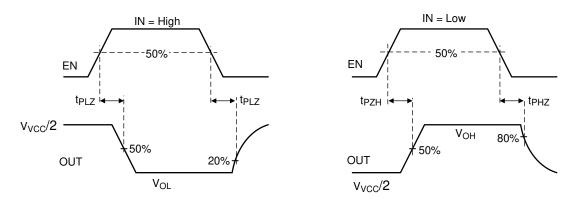


Figure 7-3. Waveforms for Driver Enable or Disable Time Measurements

8 Detailed Description

8.1 Overview

Figure 8-1 shows that the device driver output (OUT) can be used in a push-pull, high-side, or low-side configuration using the enable (EN) and transmit data (IN) input pins. OUT can drive resistive, large capacitive or large inductive loads.

TIOS101 and TIOS101x devices have integrated IEC 61000-4-4/5 EFT and surge protection. In addition, tolerance to ±65-V transients enables flexibility to choose from a wider range of TVS diodes if an application requires higher levels of protection. These integrated robustness features will simplify the system-level design by reducing the external protection circuitry.

These devices implement protection features for over-current, over-voltage and over-temperature conditions. The devices also provide a current-limit setting of the driver output current using an external resistor.

The TIOS101x devices derive the low voltage supply from the typical 24 V industrial supply via an internal linear regulator to provide power to the local controller and sensor circuitry.

8.2 Functional Block Diagrams

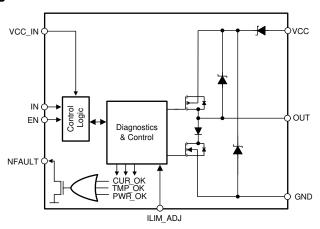


Figure 8-1. Block Diagram, TIOS101

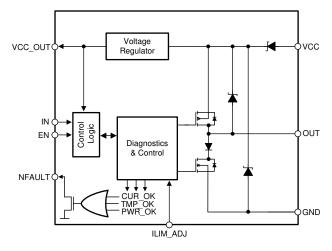


Figure 8-2. Block Diagram, TIOS101x

8.3 Feature Description

8.3.1 Current Limit Configuration

The output current can be configured with an internal resistor on ILIM_ADJ pin. The maximum settable current limit is 300 mA. This maximum setting specifies a minimum of 300 mA over temperature and voltage.

Output disable due to current fault and current fault auto recovery features can be disabled by floating ILIM_ADJ pin. However, the current fault indication is still active in this configuration. This feature is useful when driving large capacitances.

Table 8-1. Current Limitation

ILIM_ADJ Pin Condition	OUT Current Limit	NFAULT Indication During Fault	Output Disable and Auto Recovery
R _{SET} resistor to GND	Variable	Yes	Yes
Connected to GND	300 mA	Yes	Yes
OPEN	300 mA	Yes	No

8.3.2 Current Fault Detection, Indication and Auto Recovery

If the output current at OUT exceeds the internally set current limit $I_{O(LIM)}$ for a duration longer than t_{SC} , the NFAULT pin is driven logic low to indicate a fault condition. The output is turned off, but the LDO continues to function. The output periodically retries to check if the output is still in the over current condition. In this mode, the output is switched on for t_{SC} in t_{SCEN} intervals. Current fault auto recovery mode can be disabled by setting $ILIM_ADJ = OPEN$. See Table 8-3.Toggling EN will clear NFAULT.

8.3.3 Thermal Warning, Thermal Shutdown

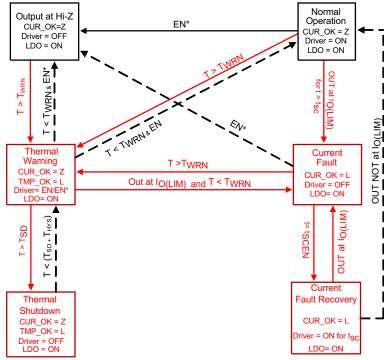
If the die temperature exceeds $T_{(WRN)}$, the NFAULT flag is held low indicating a potential over temperature problem. When the T_J exceeds $T_{(SDN)}$, The output is disabled but the LDO remains operational. As soon as the temperature drops below the temperature threshold (and after $T_{(HYS)}$), the internal circuit re-enables the driver, subject to the state of the EN and IN pins.

Submit Document Feedback

Copyright © 2021 Texas Instruments Incorporated

8.3.4 Fault Reporting (NFAULT)

NFAULT is driven low if either a current fault condition is detected, die temperature has exceeded $T_{(WRN)}$ or supply has dropped below the UVLO threshold. NFAULT returns to high-impedance as soon as all three fault conditions clear.



NFAULT = [CUR_OK && PWR_OK && TMP_OK]

Figure 8-3. Device State Diagram



8.3.5 Device Function Tables

Table 8-2. Driver Function

EN	IN	OUT	COMMENT
L / Open	X	Hi-Z	Device is in ready-to-receive state
Н	L	Н	OUT is sourcing current (high-side drive)
Н	H / Open	L	OUT is sinking current (low-side drive)

Table 8-3. Current Limit Indicator Function ($t > t_{SC}$)

				(
EN	IN	OUT CURRENT	T NFAULT COMMENT					
ы	H / Open	I _(OUT) > I _{O(LIM)}	L	OUT current exceeds the set limit for over t _{SC}				
''	тт Ореп	I _(OUT) < I _{O(LIM)}	Z	Normal operation				
П		I _(OUT) > I _{O(LIM)}	L	OUT current exceeds the set limit for over t _{SC}				
	_	I _(OUT) < I _{O(LIM)}	Z	Normal operation				
L / Open	Х	X	Z	Driver is disabled, current limit indicator is inactive				

8.3.6 The Integrated Voltage Regulator (LDO)

The TIOS1013 and TIOS1015 each have an integrated linear voltage regulator (LDO) which can supply power to external components. The voltage regulator is specified for VCC voltages in the range of 7 V to 36 V with respect to GND. The LDO is capable of delivering up to 20 mA. The LDO output is current limited to 35-mA to limit the inrush current onto VCC OUT decoupling capacitors during initial power up.

The LDO is designed to be stable with standard ceramic capacitors with values of 1 μ F or larger at the output. X5R- and X7R-type capacitors are best because they have minimal variation in value and ESR over temperature. Maximum ESR should be less than 1 Ω . With tolerance and dc bias effects, the minimum capacitance to ensure stability is 1 μ F.

Submit Document Feedback

Copyright © 2021 Texas Instruments Incorporated



8.3.7 Reverse Polarity Protection

Reverse polarity protection circuitry protects the devices against accidental reverse polarity connections to the VCC, OUT and GND pins. The maximum voltage between any of the pins may not exceed 60 V DC at any time.

Figure 8-4 and Figure 8-5 shows all the possible connection combinations.

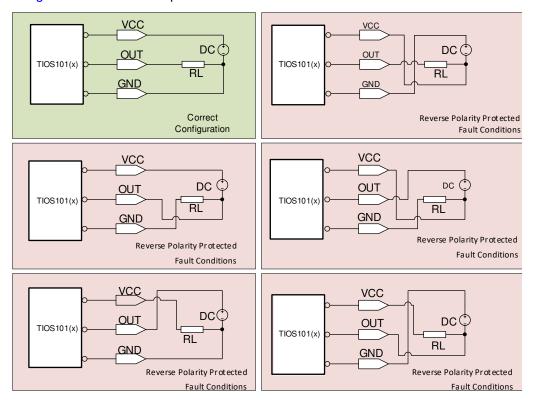


Figure 8-4. High-Side Driver Configuration



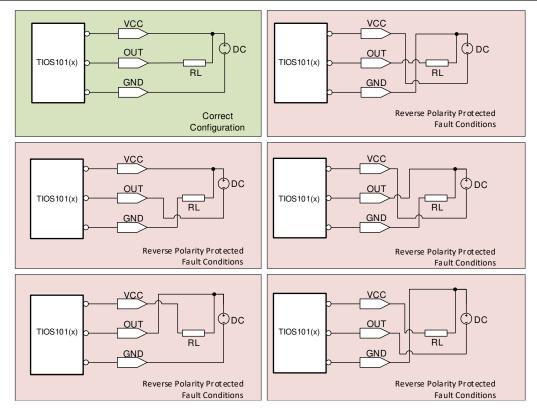
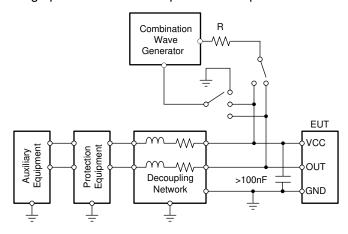


Figure 8-5. Low-Side Driver Configuration

8.3.8 Integrated Surge Protection and Transient Waveform Tolerance

The VCC and OUT pins of the device are capable of withstanding up to 1.2 kV of 1.2/50 - 8/20 μ s IEC 61000-4-5 surge with a source impedance of 500 Ω . The surge testing should be performed with a minimum 100 nF supply decoupling capacitor between VCC and GND, and 1 μ F between VCC_IN/OUT and GND.

External TVS diodes may be required for higher transient protection levels. The system designer should ensure that the maximum clamping voltage of the external diodes should be < 65 V at the desired current level. The device is capable of withstanding up to ± 65 -V transient pulses $< 100 \, \mu s$.



1.2/50 - 80/20 µs CWG R = 500 O

Figure 8-6. Surge Test Setup

8.3.9 Power Up Sequence

VCC_IN and VCC domains can be powered up in any sequence. In the event of VCC is powered and VCC_IN is not, the OUT pin remains in high impedance.

8.3.10 Undervoltage Lock-Out (UVLO)

The device enters UVLO if the VCC voltage falls below $V_{(UVLO)}$. (For the device without the integrated LDO, the device monitors VCC IN in addition to VCC. UVLO happens if either supply falls below the threshold.)

As soon as the supply falls below $V_{(UVLO)}$, NFAULT is pulled low, the LDO is turned off and the OUT output is disabled (Hi-Z). Receiver performance is not specified in this mode.

When the supply rises above $V_{(UVLO)}$, NFAULT returns to Hi-Z (given no other fault conditions present) and the LDO will be enabled immediately. The OUT output will be turned on after $T_{(UVLO)}$ delay.

8.4 Device Functional Modes

These devices can operate in three different modes.

8.4.1 NPN Configuration (N-Switch Mode)

Set IN pin high (or open) and use EN pin as control for realizing the function of an N-switch (low-side configuration) on OUT.

8.4.2 PNP Configuration (P-Switch Mode)

Set IN pin low and use EN pin as control for realizing the function of a P-switch (high-side configuration) on OUT.

8.4.3 Push-Pull Mode

Set EN pin high and toggle IN as control for realizing the function of a push-pull output on OUT. Table 8-4, Table 8-5, and Table 8-6 summarize the pin configurations to accomplish the functional modes.



Table 8-4. NPN Mode

EN	IN	OUT
L / Open	H / Open	Hi-Z
Н	H / Open	N-Switch

Table 8-5. PNP Mode

EN	IN	OUT
L / Open	L	Hi-Z
Н	L	P-Switch

Table 8-6. Push-Pull Mode

EN	IN	OUT
L / Open	X	Hi-Z
Н	H / Open	N-Switch
Н	L	P-Switch



9 Application Information Disclaimer

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

TIOS101 and TIOS101x are robust 24-V digital drivers for industrial sensors.

9.2 Typical Application

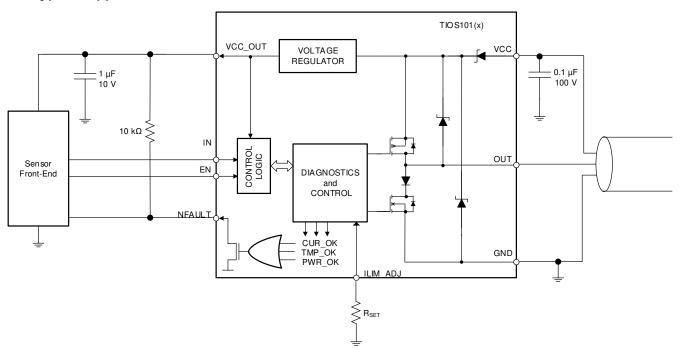


Figure 9-1. Typical Application Schematic

9.2.1 Design Requirements

Table 9-1 shows recommended components for a typical system design.

PARAMETERS VALUE Input voltage range (VCC) 24 V, 30 V (max) Output current (OUT) 200 mA Output voltage (VCC OUT), Pick TIOS1015 5 V Maximum LDO output current (I_{VCC(OUT)}) 5 mA Pull-up resistors for NFAULT 10 kΩ $0.1 \, \mu F / 100 \, V$ VCC decoupling capacitor $1 \mu F / 10 V$ LDO output capacitor ILIM_ADJ resistor (R_{SET}) $10 k\Omega$ 105°C Maximum Ambient Temperature, TA

Table 9-1. Design Parameters

9.2.2 Detailed Design Procedure

9.2.2.1 Maximum Junction Temperature Check

For a 200 mA current limit:

- The maximum driver output current limit, I_{O(LIM)} = 250 mA (allowed for current limit tolerance).
- The maximum voltage drop across the high-side switch is given with $V_{DS(ON)} = 1.75 \text{ V}$.

This causes a power consumption of:

$$PD_{OP} = V_{DS(ON)} x I_{O(LIM)} = 1.75V x 250 mA = 437.5 mW$$
 (1)

For a 5 mA LDO current output,

$$PD_{LDO} = (V_{L+} - V_{VCC_OUT}) \times I_{VCC_OUT} = (30 - 5) \text{V} \times 5 \text{ mA} = 125 \text{ mW}$$
 (2)

Total power dissipation,

$$PD = PD_{OP} + PD_{LDO} = 437.5 \, mW + 125 \, mW = 562.5 \, mW$$
 (3)

Multiply this value with the Junction-to-ambient thermal resistance of θ_{JA} = 68.1°C/W (taken from the Section 6.4 table) to receive the difference between junction temperature, T_J , and ambient temperature, T_A :

$$\Delta T = T_J - T_A = PD \times \theta_{JA} = 562.5 \, mW \times 68.1^{\circ} C/W = 38.3^{\circ} C$$
 (4)

Add this value to the maximum ambient temperature of $T_A = 105$ °C to receive the final junction temperature:

$$T_{J-max} = T_{A-max} + \Delta T = 105^{\circ}C + 38.3^{\circ}C = 143.3^{\circ}C$$
 (5)

As long as T_{J-max} is below the recommended maximum value of 150°C, no thermal shutdown will occur. However, thermal warning may occur as the junction temperature is greater than T_{WRN} .

Note that the modeling of the complete system may be necessary to predict junction temperature in smaller PCBs and/or enclosures without air flow.

9.2.2.2 Driving Capacitive Loads

These devices are capable of driving capacitive loads on the OUT output. Assuming a pure capacitive load without series/parallel resistance, the maximum capacitance that can be charged without triggering current fault can be calculated as:

$$C_{LOAD} = \frac{[I_{O(LIM)} \times t_{SC}]}{V_{(VCC)}}$$
(6)

Higher capacitive loads can be driven if a series resistor is connected between the OUT and the load. Capacitive loads can be connected to VCC and GND.

9.2.2.3 Driving Inductive Loads

The TIOS101(x) family is capable of magnetizing and demagnetizing inductive loads up to 1.5 H. These devices contain internal circuitry that enables fast demagnetization when configured as either P-switch or N-switch mode.

In P-switch configuration, the load inductor L is magnetized when the OUT pin is driven high. When the PNP is turned off, there is a significant amount of negative inductive kick back at the OUT pin. This voltage is clamped internally at about -75 V.

Similarly in N-switch configuration, the load inductor L is magnetized when the OUT pin is driven low. When the NPN is turned off, there is a significant amount of positive inductive kick back at the OUT pin. This voltage is clamped internally at about 75 V.

The equivalent protection circuits are shown in Figure 9-2 and Figure 9-3. The minimum value of the resistive load R can be calculated as:

$$R = \frac{V_{(VCC)}}{I_{O(LIM)}}$$
(7)

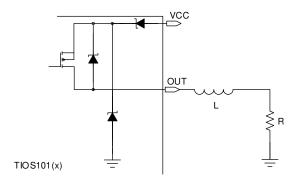


Figure 9-2. PNP Mode

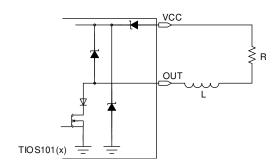
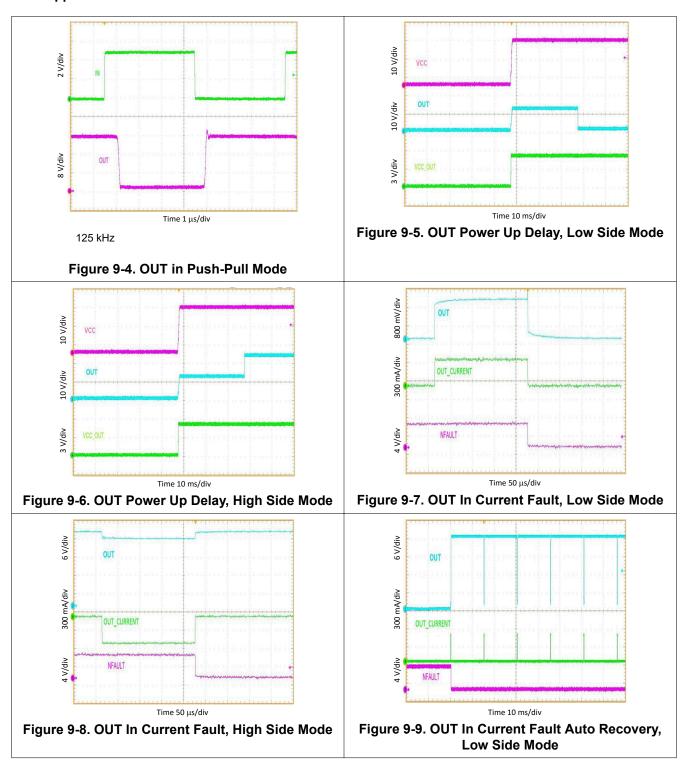
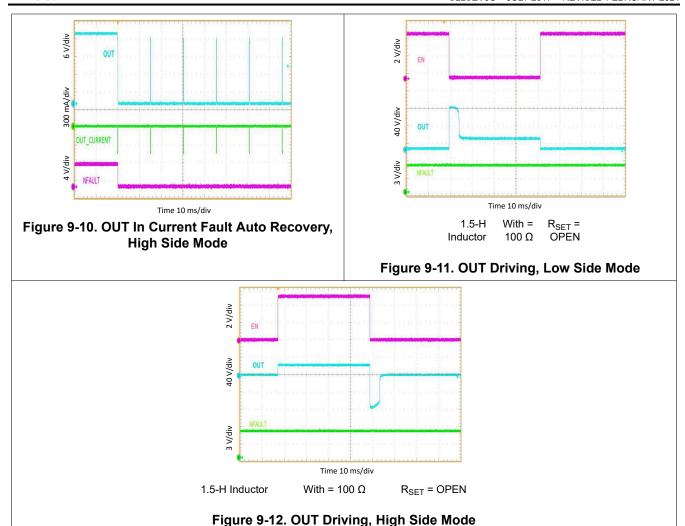


Figure 9-3. NPN Mode

9.2.3 Application Curves





10 Power Supply Recommendations

The TIOS101 and TIOS101x are designed to operate from a 24-V nominal supply at VCC, which can vary by +12 V and -17 V from the nominal value to remain within the device's recommended supply voltage range of 7 V to 36 V. This supply should be buffered with at least a 100-nF/100-V capacitor.



11 Layout

11.1 Layout Guidelines

- Use of a 4-layer board is recommended for good heat conduction. Use layer 1 (top layer) for control signals, layer 2 as GND, layer 3 for the 24-V supply plane (VCC), and layer 4 for the regulated output supply (VCC_IN/OUT).
- Connect the thermal pad to GND with maximum amount of thermal vias for best thermal performance.
- Use entire planes for VCC, VCC IN/OUT and GND to assure minimum inductance.
- The VCC terminal must be decoupled to ground with a low-ESR ceramic decoupling capacitor with a
 minimum value of 100 nF. The capacitor must have a voltage rating of 50 V minimum (100 V depending on
 max sensor supply fault rating) and an X5R or X7R dielectric.
- The optimum placement of the capacitor is closest to the VCC and GND terminals to reduce supply drops during large supply current loads. See Figure 11-1 for a PCB layout example.
- Connect all open-drain control outputs via 10 kΩ pull-up resistors to the VCC_IN/OUT plane to provide a defined voltage potential to the system controller inputs when the outputs are high-impedance.
- Connect the R_{SET} resistor between ILIM_ADJ and GND.
- Decouple the regulated output voltage at VCC_IN/OUT to ground with a low-ESR, 1 μF, ceramic decoupling capacitor. The capacitor should have a voltage rating of 10 V minimum and an X5R or X7R dielectric.

11.2 Layout Example

- VIA to Layer 2: Power Ground Plane (VCC)
- VIA to Layer 3: 24V Supply Plane (GND)
- O VIA to Layer 4: Regulated Supply Plane (VCC_IN/OUT)

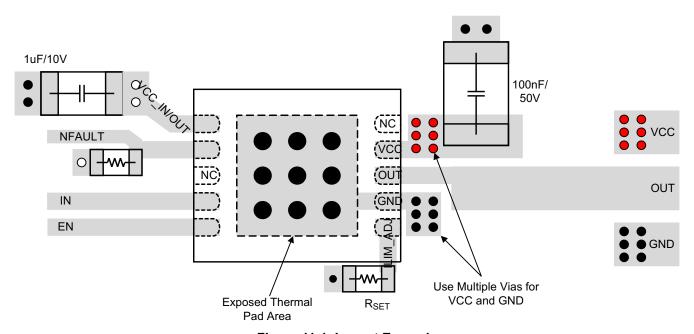


Figure 11-1. Layout Example



12 Device and Documentation Support

12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.3 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com

9-Nov-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
TIOS1013DMWR	Active	Production	VSON (DMW) 10	1500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TS1013
TIOS1013DMWR.A	Active	Production	VSON (DMW) 10	1500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TS1013
TIOS1013DMWR.B	Active	Production	VSON (DMW) 10	1500 LARGE T&R	-	Call TI	Call TI	-40 to 125	
TIOS1013DMWT	Active	Production	VSON (DMW) 10	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TS1013
TIOS1013DMWT.A	Active	Production	VSON (DMW) 10	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TS1013
TIOS1013DMWT.B	Active	Production	VSON (DMW) 10	250 SMALL T&R	-	Call TI	Call TI	-40 to 125	
TIOS1015DMWR	Active	Production	VSON (DMW) 10	1500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TS1015
TIOS1015DMWR.A	Active	Production	VSON (DMW) 10	1500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TS1015
TIOS1015DMWR.B	Active	Production	VSON (DMW) 10	1500 LARGE T&R	-	Call TI	Call TI	-40 to 125	
TIOS1015DMWT	Active	Production	VSON (DMW) 10	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TS1015
TIOS1015DMWT.A	Active	Production	VSON (DMW) 10	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TS1015
TIOS1015DMWT.B	Active	Production	VSON (DMW) 10	250 SMALL T&R	-	Call TI	Call TI	-40 to 125	
TIOS101DMWR	Active	Production	VSON (DMW) 10	1500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TS101
TIOS101DMWR.A	Active	Production	VSON (DMW) 10	1500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TS101
TIOS101DMWR.B	Active	Production	VSON (DMW) 10	1500 LARGE T&R	-	Call TI	Call TI	-40 to 125	
TIOS101DMWT	Active	Production	VSON (DMW) 10	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TS101
TIOS101DMWT.A	Active	Production	VSON (DMW) 10	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TS101
TIOS101DMWT.B	Active	Production	VSON (DMW) 10	250 SMALL T&R	-	Call TI	Call TI	-40 to 125	

⁽¹⁾ Status: For more details on status, see our product life cycle.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



PACKAGE OPTION ADDENDUM

www.ti.com 9-Nov-2025

(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



www.ti.com 29-Sep-2023

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TIOS1013DMWR	VSON	DMW	10	1500	178.0	13.5	2.75	3.35	1.05	8.0	12.0	Q2
TIOS1013DMWT	VSON	DMW	10	250	178.0	13.5	2.75	3.35	1.05	8.0	12.0	Q2
TIOS1015DMWR	VSON	DMW	10	1500	178.0	13.5	2.75	3.35	1.05	8.0	12.0	Q2
TIOS1015DMWT	VSON	DMW	10	250	178.0	13.5	2.75	3.35	1.05	8.0	12.0	Q2
TIOS101DMWR	VSON	DMW	10	1500	178.0	13.5	2.75	3.35	1.05	8.0	12.0	Q2
TIOS101DMWT	VSON	DMW	10	250	178.0	13.5	2.75	3.35	1.05	8.0	12.0	Q2



www.ti.com 29-Sep-2023

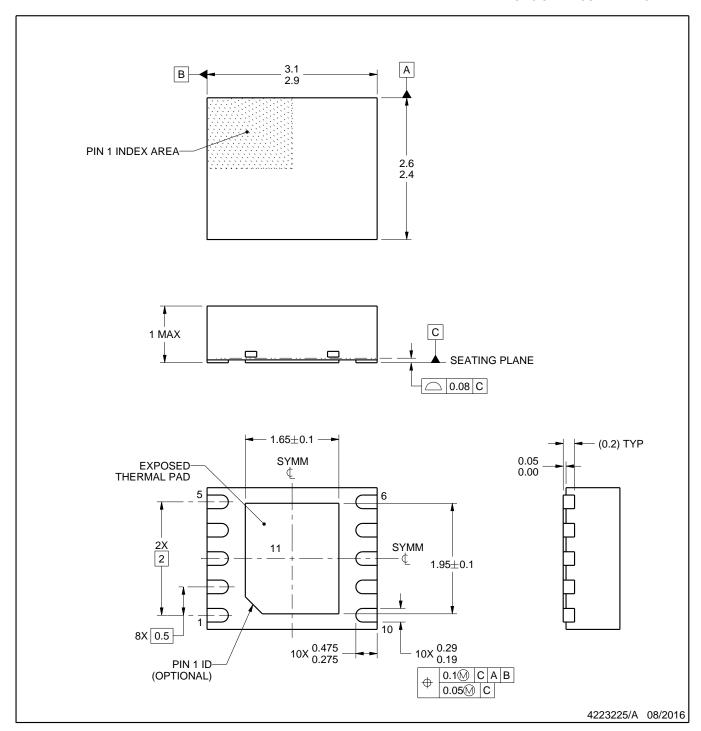


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TIOS1013DMWR	VSON	DMW	10	1500	189.0	185.0	36.0
TIOS1013DMWT	VSON	DMW	10	250	189.0	185.0	36.0
TIOS1015DMWR	VSON	DMW	10	1500	189.0	185.0	36.0
TIOS1015DMWT	VSON	DMW	10	250	189.0	185.0	36.0
TIOS101DMWR	VSON	DMW	10	1500	189.0	185.0	36.0
TIOS101DMWT	VSON	DMW	10	250	189.0	185.0	36.0



PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

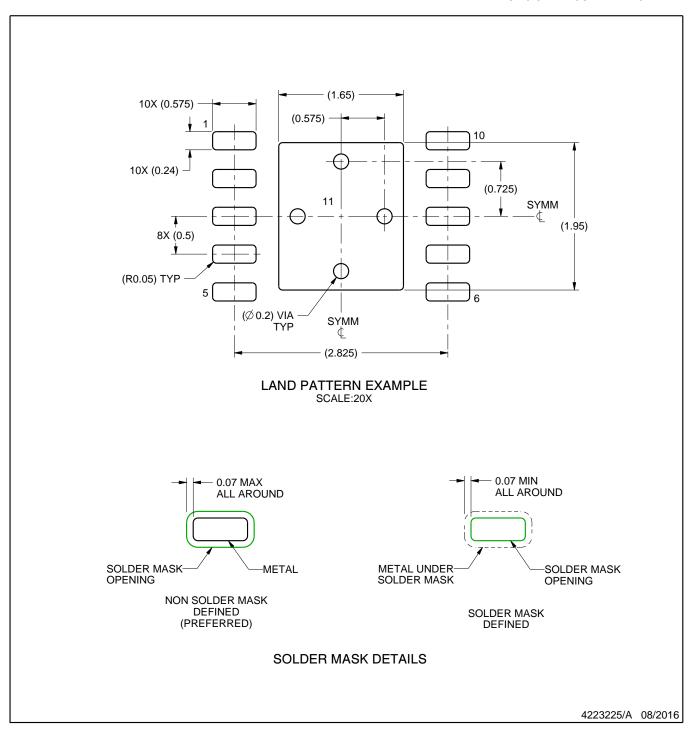
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC SMALL OUTLINE - NO LEAD

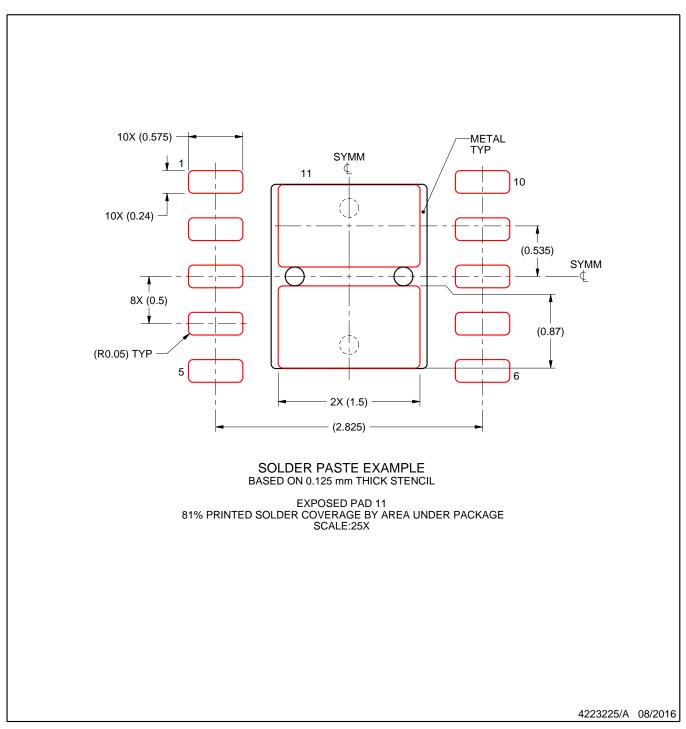


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you fully indemnify TI and its representatives against any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale, TI's General Quality Guidelines, or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products. Unless TI explicitly designates a product as custom or customer-specified, TI products are standard, catalog, general purpose devices.

TI objects to and rejects any additional or different terms you may propose.

Copyright © 2025, Texas Instruments Incorporated

Last updated 10/2025